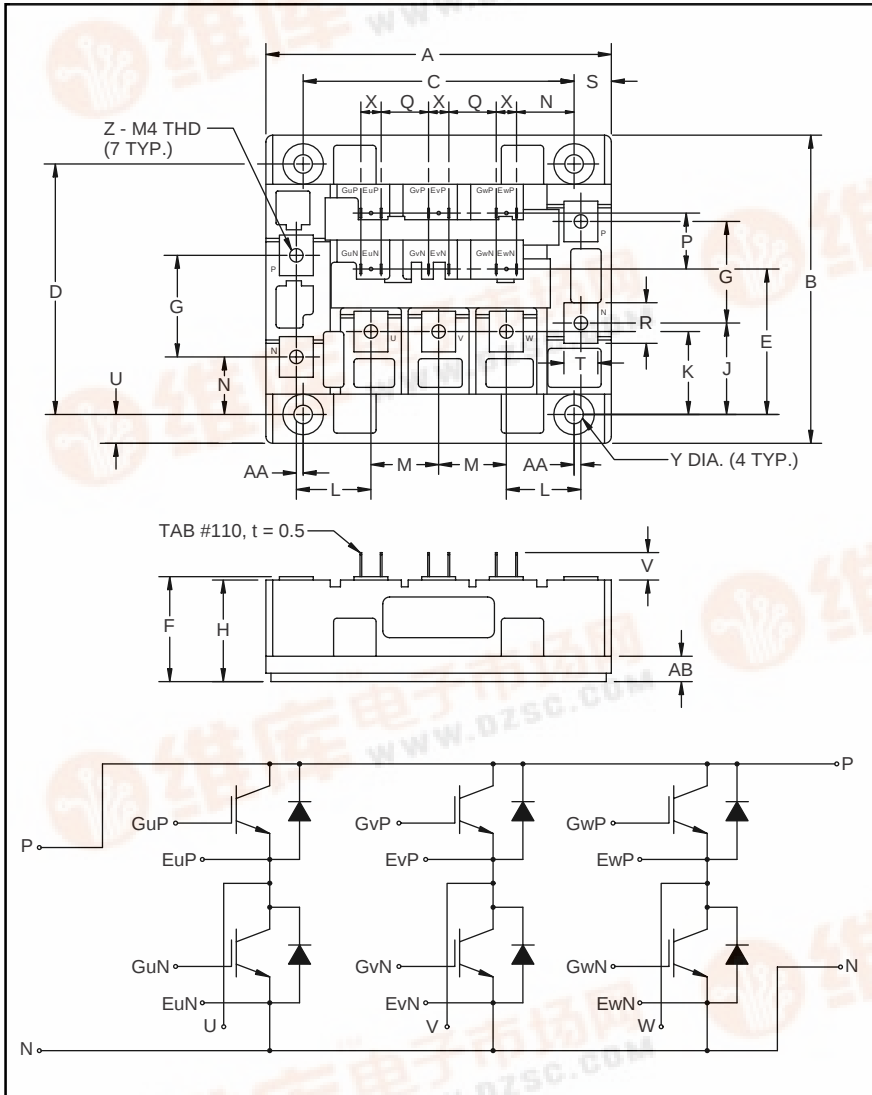


MITSUBISHI IGBT MODULES

CM75TF-12H

HIGH POWER SWITCHING USE
INSULATED TYPE



Outline Drawing and Circuit Diagram

Dimensions	Inches	Millimeters
A	4.02±0.02	102±0.5
B	3.58±0.02	91.0±0.5
C	3.15±0.01	80.0±0.25
D	2.913±0.01	74.0±0.25
E	1.69	43.0
F	1.18+0.06/-0.02	30.0+1.5/-0.5
G	1.18	30.0
H	1.16	29.5
J	1.06	27.0
K	0.96	24.5
L	0.87	22.0
M	0.79	20.0
N	0.67	17.0

Dimensions	Inches	Millimeters
P	0.65	16.5
Q	0.55	14.0
R	0.47	12.0
S	0.43	11.0
T	0.39	10.0
U	0.33	8.5
V	0.32	8.1
X	0.24	6.0
Y	0.22 Dia.	Dia. 5.5
Z	M4 Metric	M4
AA	0.08	2.0
AB	0.28	7.0



Description:

Mitsubishi IGBT Modules are designed for use in switching applications. Each module consists of six IGBTs in a three phase bridge configuration, with each transistor having a reverse-connected super-fast recovery free-wheel diode. All components and interconnects are isolated from the heat sinking baseplate, offering simplified system assembly and thermal management.

Features:

- ☐ Low Drive Power
- ☐ Low $V_{CE(sat)}$
- ☐ Discrete Super-Fast Recovery Free-Wheel Diode
- ☐ High Frequency Operation
- ☐ Isolated Baseplate for Easy

Applications:

- ☐ AC Motor Control
- ☐ Motion/Servo Control
- ☐ UPS
- ☐ Welding Power Supplies

Ordering Information:

Example: Select the complete part module number you desire from the table below -i.e. CM75TF-12H is a 600V (V_{CES}), 75 Ampere Six-IGBT Module.

Type	Current Rating Amperes	V_{CES} Volts (x 50)
CM	75	12

CM75TF-12H

HIGH POWER SWITCHING USE
INSULATED TYPEAbsolute Maximum Ratings, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Ratings	Symbol	CM75TF-12H	Units
Junction Temperature	T_j	-40 to 150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-40 to 125	$^{\circ}\text{C}$
Collector-Emitter Voltage (G-E SHORT)	V_{CES}	600	Volts
Gate-Emitter Voltage (C-E SHORT)	V_{GES}	± 20	Volts
Collector Current ($T_C = 25^{\circ}\text{C}$)	I_C	75	Amperes
Peak Collector Current	I_{CM}	150*	Amperes
Emitter Current** ($T_C = 25^{\circ}\text{C}$)	I_E	75	Amperes
Peak Emitter Current**	I_{EM}	150*	Amperes
Maximum Collector Dissipation ($T_C = 25^{\circ}\text{C}$, $T_j \leq 150^{\circ}\text{C}$)	P_C	310	Watts
Mounting Torque, M4 Main Terminal	—	0.98 ~ 1.47	$\text{N} \cdot \text{m}$
Mounting Torque, M5 Mounting	—	1.47 ~ 1.96	$\text{N} \cdot \text{m}$
Weight	—	540	Grams
Isolation Voltage (Main Terminal to Baseplate, AC 1 min.)	V_{iso}	2500	V_{rms}

*Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j(max)}$ rating.

**Represents characteristics of the anti-parallel, emitter-to-collector free-wheel diode (FWDI).

Static Electrical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Collector-Cutoff Current	I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0\text{V}$	—	—	1.0	mA
Gate Leakage Current	I_{GES}	$V_{GE} = V_{GES}$, $V_{CE} = 0\text{V}$	—	—	0.5	μA
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$I_C = 7.5\text{mA}$, $V_{CE} = 10\text{V}$	4.5	6.0	7.5	Volts
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 75\text{A}$, $V_{GE} = 15\text{V}$	—	2.1	2.8**	Volts
		$I_C = 75\text{A}$, $V_{GE} = 15\text{V}$, $T_j = 150^{\circ}\text{C}$	—	2.15	—	Volts
Total Gate Charge	Q_G	$V_{CC} = 300\text{V}$, $I_C = 75\text{A}$, $V_{GE} = 15\text{V}$	—	225	—	nC
Emitter-Collector Voltage	V_{EC}	$I_E = 75\text{A}$, $V_{GE} = 0\text{V}$	—	—	2.8	Volts

** Pulse width and repetition rate should be such that device junction temperature rise is negligible.

Dynamic Electrical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Input Capacitance	C_{ies}	$V_{GE} = 0\text{V}$, $V_{CE} = 10\text{V}$	—	—	7.5	nF
Output Capacitance	C_{oes}		—	—	2.6	nF
Reverse Transfer Capacitance	C_{res}		—	—	1.5	nF
Resistive	Turn-on Delay Time	$V_{CC} = 300\text{V}$, $I_C = 75\text{A}$, $V_{GE1} = V_{GE2} = 15\text{V}$, $R_G = 8.3\Omega$	—	—	120	ns
	Rise Time		—	—	300	ns
Switching	Turn-off Delay Time		—	—	200	ns
Times	Fall Time		—	—	300	ns
Diode Reverse Recovery Time	t_{rr}	$I_E = 75\text{A}$, $di_E/dt = -150\text{A}/\mu\text{s}$	—	—	110	ns
Diode Reverse Recovery Charge	Q_{rr}	$I_E = 75\text{A}$, $di_E/dt = -150\text{A}/\mu\text{s}$	—	0.20	—	μC

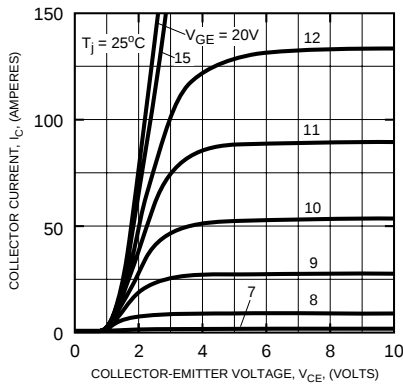
Thermal and Mechanical Characteristics, $T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

Characteristics	Symbol	Test Conditions	Min.	Typ.	Max.	Units
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per IGBT	—	—	0.40	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Case	$R_{th(j-c)}$	Per FWDi	—	—	0.90	$^{\circ}\text{C}/\text{W}$
Contact Thermal Resistance	$R_{th(c-f)}$	Per Module, Thermal Grease Applied	—	—	0.033	$^{\circ}\text{C}/\text{W}$

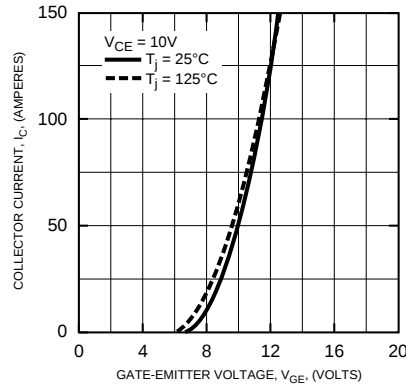
CM75TF-12H

HIGH POWER SWITCHING USE
INSULATED TYPE

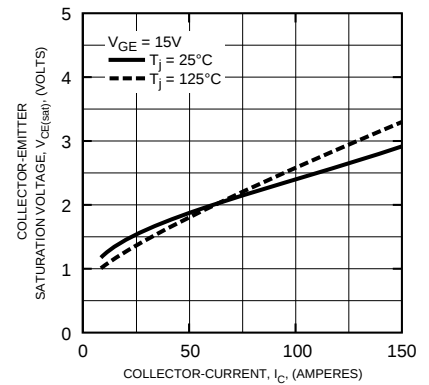
OUTPUT CHARACTERISTICS
(TYPICAL)



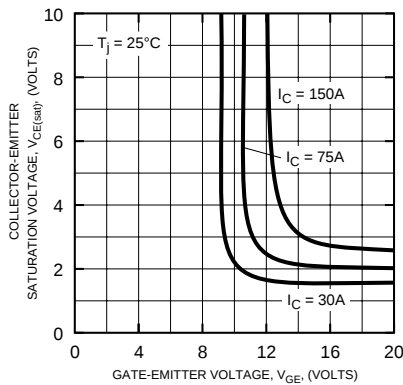
TRANSFER CHARACTERISTICS
(TYPICAL)



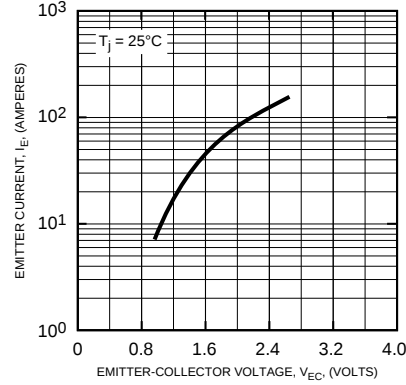
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



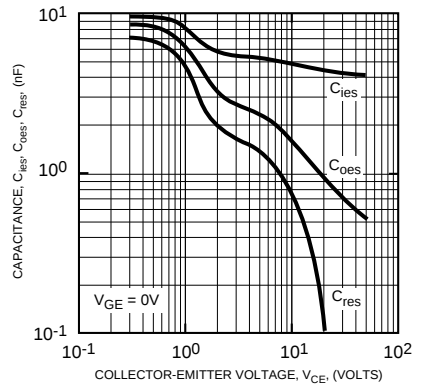
COLLECTOR-EMITTER
SATURATION VOLTAGE CHARACTERISTICS
(TYPICAL)



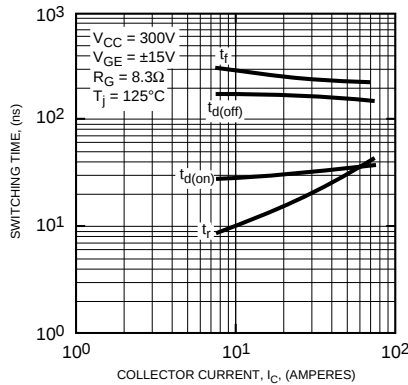
FREE-WHEEL DIODE
FORWARD CHARACTERISTICS
(TYPICAL)



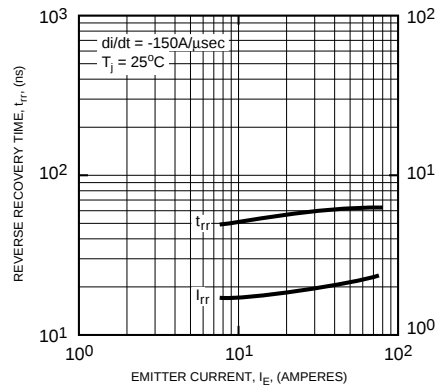
CAPACITANCE VS. V_{CE}
(TYPICAL)



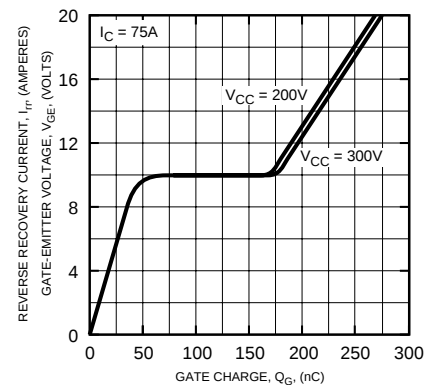
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)



REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)



GATE CHARGE, V_{GE}



CM75TF-12H

HIGH POWER SWITCHING USE
INSULATED TYPE

